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Ab-initio calculations of strain induced relaxed shape armchair graphene nanoribbon

Sanjay Prabhakar¹ and Roderick Melnik^{1,2}

¹The MS2Discovery Interdisciplinary Research Institute, M2NeT Laboratory,
Wilfrid Laurier University, Waterloo, ON N2L 3C5, Canada

²BCAM, Alameda Mazarredo 14, 48080 Bilbao, Spain

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An odd number of zigzag edges in armchair graphene nanoribbons and their mechanical properties (e.g., Young's modulus, Poisson ratio and shear modulus) have potential interest for bandgap engineering in graphene based optoelectronic devices. In this paper, we consider armchair graphene nanoribbons passivated with hydrogen at the armchair edges and then apply the strain for tuning the bandgaps. Using density functional theory calculations, our study finds that the precise control of strain can allow tuning the bandgap from semiconductor to metallic and then again switching back to semiconductor. In addition, we also show that the strained graphene nanoribbon passivated with hydrogen molecules can have large out-of-plane deformations demonstrating the properties of relaxed shape graphene. We express the strain induced by hydrogen in terms of binding energy. Finally, we characterise the effect of strain on the mechanical properties that can be used for making straintronic devices based on graphene nanoribbons.

I. INTRODUCTION

The thinnest two dimensional (2D) materials, e.g., graphene, MoSe₂ and other TMDs materials have potential interest for making next generation optoelectronic, spintronic, straintronic devices that might have performance better than conventional silicon devices¹⁻⁸. For example, the measurement of charge mobility in the graphene CMOS devices is far better than the best silicon devices^{7,9-13}. Evidence from experimental measurements confirmed that 2D materials possess unique physical properties, e.g. half integer quantum Hall effect, non-zero Berry curvature and Zak's phase, high mobility charge carriers^{7,9,14-17}. Although graphene as a material is exciting at the level of making optoelectronic devices, its bandgap opening is still one of the biggest challenges, e.g. graphene does not have any bandgaps at the Dirac point. However, by using several state-of-the-art techniques and possibility of considering different 2D materials, e.g. MoSe₂, one can easily control the bandgaps. Also, a small bandgap opening in graphene is achieved by considering the effect of spin-orbit coupling, strain and magnetic field. One can also make optoelectronic devices from armchair graphene nanoribbons, which possess a large bandgap opening at the Γ -point¹⁸⁻²³. In these armchair graphene nanoribbon devices, bandgaps can be created in a desired fashion by precise control of the width of the nanoribbon.

Strain engineering in graphene is promising for straintronic and spintronic applications. Possible ways of creating strain in graphene is to modify the in-plane and out-of-plane deformations among the carbon atoms. For examples, in plane and out-of-plane deformations in graphene can lead to the formation of relaxed shape graphene²⁴⁻²⁶. When graphene is relaxed due to precise edge engineering, the localized eigenstates, created due to strain engineering, can lead to several observed interesting phenomena such as conduction and valence band crossings, spin hot spots as well as measurements of de-

coherence time^{24,25,27,28}. Large in-plane and out-of-plane deformations can also be made by growing graphene on a flexible substrate, where not only the lattice mismatch between graphene and the substrate induces strain but also the flexible substrate can be bended for the purpose of inducing strain^{29,30}. Ripples and wrinkles in graphene are also of potential interest for band engineering applications^{24,25,31-34}. Edge functionalization of graphene nanoribbons by -H, -H₂, -O, -Br can also lead to in-plane and out-of-plane deformations and can be used for engineering of graphene bandgaps^{31,35-38}.

The mechanical properties, e.g. the Poisson ratio, Young's and shear moduli, of graphene have been characterized by using both experimental and theoretical techniques^{26,39-49}. The experimental value of Young's modulus of bulk graphite is 0.02 TPa⁵⁰ but its value for stack of graphene sheets is 0.5 TPa⁵¹, for a monolayer of graphene oxide is 0.15 TPa⁵² and for a free-standing monolayer graphene membrane is 0.1 TPa⁵³. In Ref.⁵³, authors also reported that the intrinsic breaking strength of graphene as 10 GPa. Ab initio calculations of graphene find the value of Young's modulus to be 1.11 TPa in Ref.⁵⁴ and to be 1.24 TPa in Ref.⁵⁵, where thickness of graphene is 0.34nm. By using the semiempirical nonorthogonal tight-binding (TB) method, the Young's modulus of graphene is reported as 1.206 TPa⁵⁶. In summary, the values of Young's modulus reported recently are in close agreement between experimental and theoretical studies within numerical errors⁵⁷⁻⁶¹. Hence, it is confirmed that the values of Young's modulus are extremely large in comparison to other conventional semiconductor materials. Therefore, finding the value of graphene Young's modulus in several different conditions is important for the applications in designing the devices for straintronic, spintronic and optoelectronic applications.

In this paper, we consider armchair graphene nanoribbons functioning their armchair edges by -H and -H₂. We then apply compressive strain to the system along y-direction and tensile strain along x-direction. This

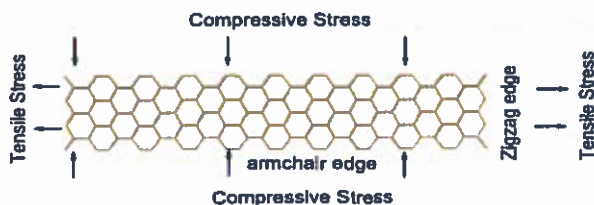


FIG. 1. (color online) Schematics of 7 zigzag edges of armchair graphene nanoribbon. We apply compressive stress at the armchair edge while tensile stress at the zigzag edge. Such type of strain engineering allow us to investigate the influence of strain on the bandengineering of graphene nanoribbon.

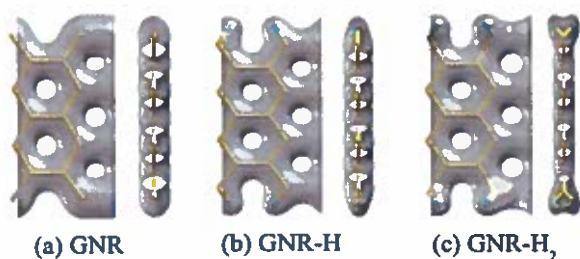


FIG. 2. (color online) Isosurface charge distributions of armchair graphene nanoribbon for (a) bare graphene (b) armchair edge functioning with hydrogen (H) and (c) armchair edge functioning with hydrogen molecule ($-H_2$). The isovalue of isosurface charge density is chosen as 0.5.

leads with possible application connected with opening and closing the bandgaps. In other words, the armchair graphene nanoribbons can be used for dual purposes of semiconductor and metallic. Within density functional theory calculations, our study show that the graphene and graphene with $-H$ functional group can not induce significant values of out-of-plane deformations while graphene with $-H_2$ functional group does induce large out-of-plane deformations exhibiting the properties of relaxed shape graphene²⁶. Such strain engineering can lead to tuning the bandgaps from semiconductor to metal and then again switching back to semiconductor. The binding energy calculations of hydrogen on graphene allow to quantify the effect of strain on the bandengineering of graphene nanoribbons. Finally, we discuss the effect of strain on the Poisson ratio, Young's and shear moduli of graphene nanoribbons.

The paper is organized as follows. In Sec. II, we provide computational details of density functional theory calculations for generating strain on graphene nanoribbon. In Sec. III, we present the results for bandengineering, poisson ratio, Young's and shear moduli of graphene, graphene edge functioning with H and H_2 . Finally, in Sec. IV, we summarize our results.

II. COMPUTATIONAL METHODS

Density Functional Theory (DFT) calculations for 7 zigzag edges of armchair graphene nanoribbons are performed in the Quantum Espresso software package⁶², where periodic boundary conditions are implemented in the simulations. Ultrasoft pseudopotentials and plane wave basis set with a kinetic energy and charge density cut-off at 100Ry and 800Ry are used. We include exchange and correlation effects within the Perdew-Burke-Ernzerhof (PBE) Functional⁶³. Van der Waals interactions are also included with the Semiempirical Grimme's DFT-D2 corrections term⁶⁴. We use orthorhombic $4.34\text{\AA} \times 24.78\text{\AA} \times 15.01\text{\AA}$ size of supercell that contains 7 zigzag edges of an armchair graphene nanoribbon. In the supercell, we have 14 atoms for the graphene nanoribbon, 18 atoms for the graphene nanoribbon with armchair edge functioning with H and 22 atoms for the graphene nanoribbon with armchair edge functioning with H_2 . During geometry optimization, all atoms in all the three directions and x-axis of the supercell are fully relaxed until the forces on atoms are smaller than 0.01 eV/\AA . We have tested several k-point samplings and calculations are performed at $(6,1,3)$ k -points sampling fulfilling the above convergence criteria. The optimized lattice parameters along the x-direction are 4.34\AA for graphene, 4.29\AA for graphene with armchair edge functioning with H , 4.30\AA for graphene with armchair edge functioning with H_2 . The optimized widths (distance between C-C atoms) of 7 zigzag edges of armchair graphene nanoribbons are 7.1353\AA (bare graphene), 7.33\AA (graphene edge functioning with H), 7.56\AA (graphene edge functioning with H_2). The XCRYSDEN program was used to draw the molecular structure⁶⁵. For strain engineering of graphene nanoribbons, we have applied the compressive stress through the armchair edge and then frozen the y-coordinates of the armchair edge atoms while allowing the other coordinates to be fully relaxed. We also fully relaxed the x-axis of the supercell.

III. RESULTS AND DISCUSSIONS

Bandgaps of the armchair graphene nanoribbon depend on the width of the ribbon. If the armchair nanoribbon contains an odd number of zigzag edges then the armchair graphene nanoribbon possesses a finite bandgap opening at the Γ point and interesting for making semiconductor devices. For an even number of zigzag edges, the armchair graphene nanoribbon has a zero band gap opening and thus possesses metallic properties. When strain is implemented in the armchair graphene nanoribbon with odd number of zigzag edges, then width of the graphene nanoribbon either decreases or increases depending on which kind of strain is applied at the boundaries of the nanoribbon. Hence, large modification of band gaps are expected due to application of strain. For example, strain induced by compressive stress re-

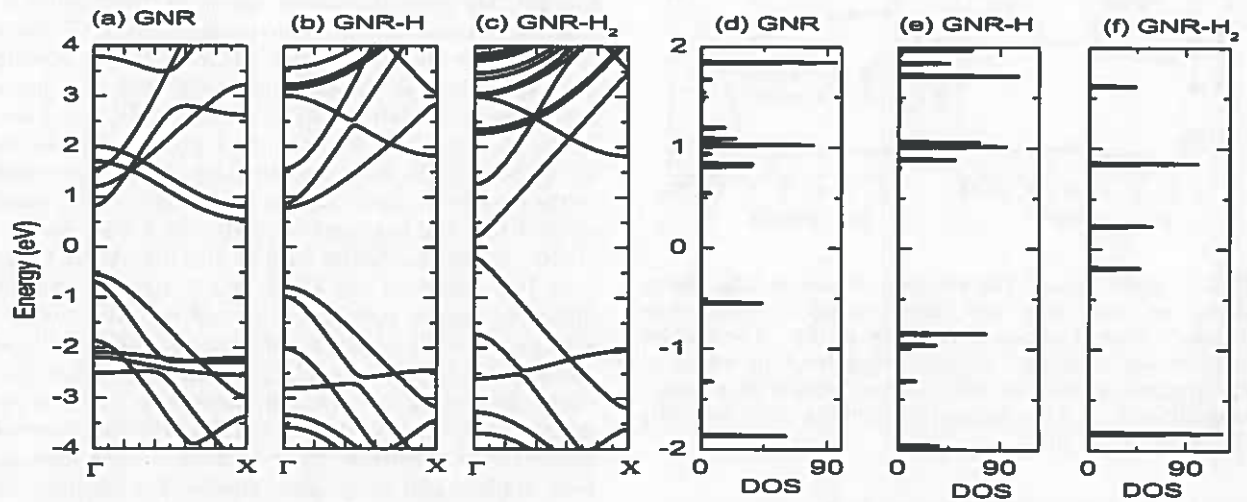


FIG. 3. (color online) Band structures and Density of States (DOS) of graphene nanoribbon, graphene nanoribbon armchair edge functioning with H, and graphene nanoribbon armchair edge functioning with H_2 .

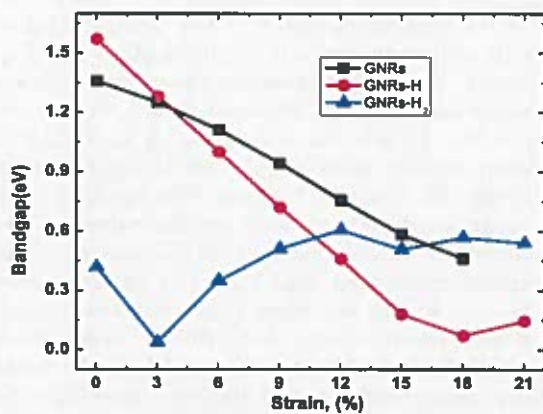


FIG. 4. (color online) Band engineering in the armchair graphene nanoribbon with the application of strain in three cases: (a) graphene nanoribbon, (b) graphene nanoribbon functioning with hydrogen at the armchair edge and (c) graphene nanoribbon functioning with H_2 molecule at the armchair edge. We see that the bandgap completely closes at the particular value of strain for the case of graphene nanoribbons functioning with H and H_2 . Here, the magnitude of strain is measured as a reference from unstrained GNRs (Fig. 3) by applying compression stress through the armchair edges (Fig. 1).

duces the width of the ribbon while tensile stress increases the width of the ribbon. Since the bandgap of graphene nanoribbon depends on the width of the ribbon, we expect the fine tuning of bandgaps with application of strain from semiconductor to metal or viceversa. In this paper, we are interested in tuning the bandgap

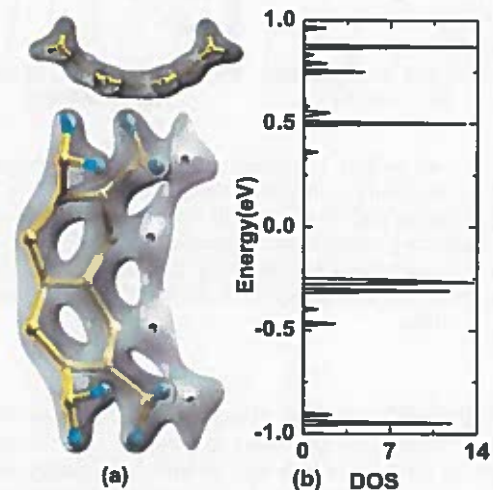


FIG. 5. (color online) Isosurface charge distribution in (a) and energy vs density of states in (b) of armchair graphene nanoribbon for armchair edge functioning with hydrogen molecule ($-H_2$) under 15% compressive strain. Notice that the out-of-plane deformations are significantly large that provided the relaxed shape graphene nanoribbon similar to Ref.^{25,26}. The isovalue of isosurface charge density is chosen as same as to be in Fig. 2.

from a semiconducting to metallic and then bringing it back to the semiconductor with the application of strain engineering. Hence, we consider the 7 zigzag edges of the armchair graphene nanoribbon and then apply the compressive stress at the armchair edge. The armchair ribbon is also allowed to elongate in the x-direction. The

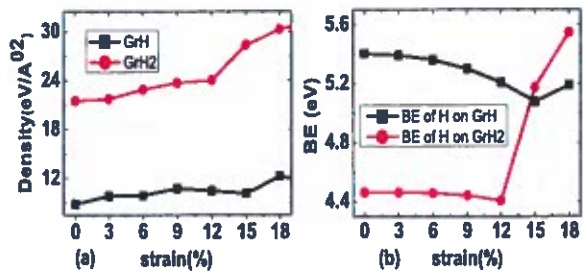


FIG. 6. (color online) The variation of relative total energy density vs strain in (a) and binding energy of hydrogen on armchair edge of graphene vs strain in (b). The relative total energy is obtained by subtracting the total energy of the graphene nanoribbon from the total energy of graphene nanoribbon with $-H$ (diamond-black in Fig. 6(a)) and $-H_2$ (circle-red in Fig. 6(a)).

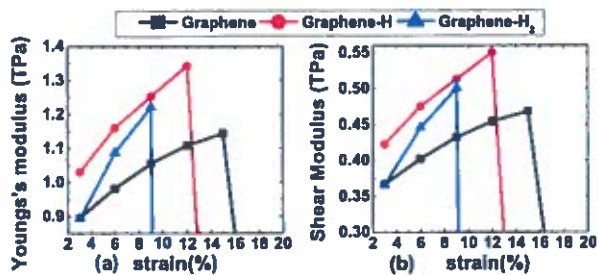


FIG. 7. (color online) The variation of Young's modulus with respect to strain in (a) and shear modulus vs strain in (b). Evidently, Young's and shear moduli increase as we increase the strain until they reach their saturation values. The Young's modulus is calculated by using Eq. 2 and shear modulus is calculated by the use of Eq. 3. Here we consider the Poisson ratio, $\nu = 0.22$.

schematics of the strained armchair graphene nanoribbon is shown in Fig. 1. One may consider 9, 11, 14 and so on and so forth armchair GNRs and then apply similar kind of compressive stress at the armchair edges for tuning the bandgaps. However in this case, the bandgaps opening at Γ -point is smaller than 7 armchair GNRs and thus we expect bandgap closing at lower values of strain. On the other hand, one may consider 5 and 3 armchair GNRs but the bandgap opening in such nanoribbon is larger than 7 armchair GNRs and hence one may need to apply large strain (larger than 18% as seen zero band gap in 7 armchair GNRs) to close the bandgaps, which may be impractical for the experiment. It is also possible to consider the odd number of armchair edges of the GNRs and then apply the strain so that one can tune the properties of bandgaps from metal to semiconductor.

In Fig. 2, we have plotted the isosurface charge distributions on 7 zigzag edges of armchair GNRs for three different cases: (i) bare GNRs (Fig. 2 (a)), (ii) GNRs with H at the armchair edge (Fig. 2 (b)) and (iii) GNRs

with H₂ at the armchair edge. As can be seen in Fig. 2, the distributions of isosurface charge in these GNRs are different because different functional groups in GNRs induce slightly different strains. Hence bandgap opening of these ribbons are expected to be different. The bandstructures and density of states of these GNRs are shown in Fig. 3. Irregularities in the mesh grid throughout the structure of GNRs may cause to induce some sharp peaks in the density of states plots in Fig. 3 and 5. At Γ point, we find that the bandgaps of GNRs are 1.36eV for bare GNRs, 1.57eV for GNRs with H and 0.42eV for GNRs with H₂. Since all the GNRs has 7 zigzag edges but different bandgap openings, it clearly indicates that the attachment of hydrogen at the armchair edge plays an important role in the bandgap engineering. More precisely, decorating the armchair edge with different elements modify the band gaps significantly due to modification of the width of the ribbon as well as inducing both in-plane and out-of-plane ripples. For example, the attachment of hydrogen changes the width, $d(C-C)$, of the ribbon (7.13Å vs 7.32Å vs 7.54Å) and also induces the in-plane and out-of-plane deformations³⁶.

The tuning of the bandgaps from semiconductor to metal and bring it back to semiconductor can be achieved by applying external strain through the armchair edge, as shown schematically in Fig.1. The bandgap engineering with respect to strain is shown in Fig. 4. In Fig. 4 (diamond), we find that graphene always stays as a semiconductor even for large values of strain. On the other hand, in Fig. 4(circle) the armchair edge passivated with hydrogen become metallic (i.e., no bandgap) approximately at 18% of applied strain. The bandgap closing can be achieved even at much smaller values of strain (approximately at 3% of strain) for the case of graphene nanoribbon passivated with H₂. The bandgap closing can be seen due to the effect of strain because applied strain decreases the width of the ribbon. When the ribbon width becomes closer to the width of the 6 (even number) zigzag edge armchair graphene nanoribbon then the metallic behavior in the band engineering of graphene nanoribbon can be seen^{66,67}.

Using finite element method simulations, authors in Ref.^{25,26} have shown that the relaxed shape graphene nanoribbon has potential interest for graphene-based strain engineering devices²⁸ as well as for the observation of quantum phenomena e.g. discrete energy levels, pseudospin decoherence time and nontrivial topological phases^{16,24,66,67}. When the out-of-plane deformations are large as can be seen in Fig. 5(a) for the case of graphene passivated with hydrogen, we observe a relaxed shape graphene nanoribbon. In Fig. 5(b) we have plotted the density of states and find the bandgap reopening in the graphene nanoribbon.

Now we turn to the discussions of mechanical properties observed in the armchair graphene nanoribbon due to externally applied compressive strain from the y-direction and tensile strain in the x-direction.

In Fig. 6(a), we plot the relative total energy density

(i.e., energy density difference relative to graphene). This total energy is used to calculate the Young's modulus, shear modulus and the binding energy of hydrogen. In this figure, we find that the total energy density increases significantly for the case of graphene passivated with $-H_2$ molecules (circles) at 12% of strain which provides an indication of relaxed shape graphene (i.e., very large out-of-plane deformations)²⁶. In Fig. 6 (b), we plot the binding energy of hydrogen in the graphene. The binding energy calculation allows us to characterize whether H or H_2 is energetically favourable to the armchair edge of the graphene nanoribbon. The binding energy is found by using the expression:⁶⁸

$$BE = U[Gr(H, H_2)] - U[Gr] - U[H], \quad (1)$$

where BE is the binding energy, $U[Gr(H, H_2)]$ is the total energy of graphene with passivation layer, $U[Gr]$ is the total energy of graphene and $U[H]$ is the total energy of hydrogen in vacuum. As can be seen in Fig. 6 (b), the binding energy of hydrogen in the graphene passivated with $-H_2$ enhances significantly after 12% of strain, which provides a clear indication of very large out-of-plane deformations, as can be seen in the optimized structure in Fig. 5. As can be seen in Fig. 6(b), the binding energy of H on graphene-H is larger than H on graphene- H_2 (approximately less than 12% strain) and hence hydrogen on graphene-H is energetically more favorable. However, when the out-of-plane deformations are large due to large strain then the binding energy of H on graphene- H_2 is larger and hence H_2 functional group become energetically more favourable.

Finally, we investigate the effect of strain on the Young's modulus, Poisson ratio and shear modulus of graphene nanoribbon. The Young's modulus is calculated by using the expression⁴¹

$$Y = \frac{1}{A_0} \frac{d^2U}{d\varepsilon_y^2}, \quad (2)$$

where A_0 is the optimized area without imposing any strain, U is the total energy, and ε_y is the externally applied compressive strain. In Fig. 7(a), we find that the Young's modulus of graphene passivated with H_2 is larger than the Young's modulus of graphene and graphene passivated with H. Young's modulus also increases as we increase the strain and then sharply decreases providing an indication of saturation value of the Young's modulus. The numerical values of Young's modulus presented in Fig. 7(a) are consistent with the experimental and theoretical values reported in the literature.^{26,41-48}

The Poisson ratio is another important physical quantity characterizing the mechanical properties of materials^{41-43,69}. By applying compressive external strain, ε_y , in the graphene in the y-direction, and by using the supercell of DFT calculations to record the resulted strain in the x-direction, ε_x , we find the Poisson ratio from the

expression, $\nu = \varepsilon_x/\varepsilon_y$ as $\nu = 0.25$ for graphene, $\nu = 0.25$ for graphene passivated with H and $\nu = 0.22$ for graphene passivated with H_2 . Since the Poisson ratios for all three cases are almost the same ($\nu = 0.25$ (Gr), 0.25 (Gr-H), and 0.22 (Gr- H_2)), we can draw a conclusion that the Poisson ratio of graphene is unaffected by the passivation of -H and H_2 at the armchair edge.

After calculating the Young's modulus and Poisson ratio, we can finally find the shear modulus, G , by using the expression,

$$G = \frac{Y}{2(1+\nu)}. \quad (3)$$

The shear modulus with respect to applied compressive strain is plotted in Fig. 7(b). Similar to Young's modulus, shear modulus also increases as we increase the strain until it reaches to the saturation value.

IV. CONCLUSION

In summary, we have studied the effect of strain on the band engineering (e.g., semiconductor vs metallic) and the mechanical properties (e.g. Young's modulus, shear modulus and Poisson ratio) of armchair graphene nanoribbons passivated with hydrogen and hydrogen molecules at the armchair edges. We have shown that the strain can be used for tuning the bandgap from semiconductor to metallic, and then strain can again be used to tune the bandgaps from metallic characteristics to semiconductor. We have also shown that at the large values of strain in graphene nanoribbons passivated with hydrogen molecules, large out-of-plane deformations in graphene nanoribbon can show the properties of relaxed shape graphene. We have quantified the strain induced by hydrogen molecules on graphene nanoribbons in terms of the binding energy. Finally, we have shown that the Young's and shear moduli increase as we increase the strain until they reach to their maximum values while the Poisson ratio is independent to the passivation materials. Our findings of bandgap tuning and exploration of mechanical properties can be used in designing novel optoelectronic devices, as well as for straintronic applications.

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- ¹ C. Androulidakis, E. Koukaras, M. Poss, K. Papagelis, C. Galiotis, and S. Tawfick, *Physical Review B* **97**, 241414 (2018).
- ² A. Mannix, Z. Zhang, N. Guisinger, B. Yakobson, and M. Hersam, *Nature nanotechnology* **13**, 444 (2018).
- ³ R. Wu, I. K. Drozdov, S. Eltinge, P. Zahl, S. Ismail-Beigi, I. Božović, and A. Gozar, *Nature nanotechnology* , 1 (2018).
- ⁴ L. Feng, K. Yabuoshi, Y. Sugimoto, J. Onoda, M. Fukuda, and T. Ozaki, *Physical Review B* **98**, 195311 (2018).
- ⁵ A. K. Geim and K. S. Novoselov, *Nature materials* **6**, 183 (2007).
- ⁶ J. N. Coleman, M. Lotya, A. O'Neill, S. D. Bergin, P. J. King, U. Khan, K. Young, A. Gaucher, S. De, R. J. Smith, I. V. Shvets, S. K. Arora, G. Stanton, H.-Y. Kim, K. Lee, G. T. Kim, G. S. Duesberg, T. Hallam, J. J. Boland, J. J. Wang, J. F. Donegan, J. C. Grunlan, G. Moriarty, A. Shmeliov, R. J. Nicholls, J. M. Perkins, E. M. Grieverson, K. Theuvsen, D. W. McComb, P. D. Nellist, and V. Nicolosi, *Science* **331**, 568 (2011).
- ⁷ N. Savage, *Nature* **483**, S30 (2012).
- ⁸ S. Manzeli, D. Ovchinnikov, D. Pasquier, O. V. Yazyev, and A. Kis, *Nature Reviews Materials* **2**, 17033 (2017).
- ⁹ K. S. Novoselov, A. K. Geim, S. V. Morozov, D. Jiang, Y. Zhang, S. V. Dubonos, I. V. Grigorieva, and A. A. Firsov, *Science* **306**, 666 (2004).
- ¹⁰ L. Liao, Y.-C. Lin, M. Bao, R. Cheng, J. Bai, Y. Liu, Y. Qu, K. L. Wang, Y. Huang, and X. Duan, *Nature* **467**, 305 (2010).
- ¹¹ T. Yang, B. Zheng, Z. Wang, T. Xu, C. Pan, J. Zou, X. Zhang, Z. Qi, H. Liu, Y. Feng, *et al.*, *Nature communications* **8**, 1906 (2017).
- ¹² J. S. Friedman, A. Girdhar, R. M. Gelfand, G. Memik, H. Mohseni, A. Taflovv, B. W. Wessels, J.-P. Leburton, and A. V. Sahakian, *Nature communications* **8**, 15635 (2017).
- ¹³ A. Altıntaş, K. Çakmak, and A. D. Güçlü, *Physical Review B* **95**, 045431 (2017).
- ¹⁴ K. S. Novoselov, A. K. Geim, S. V. Morozov, D. Jiang, M. I. Katsnelson, I. V. Grigorieva, S. V. Dubonos, and A. A. Firsov, *Nature* **438**, 197 (2005).
- ¹⁵ K. S. Novoselov, D. Jiang, F. Schedin, T. J. Booth, V. V. Khotkevich, S. V. Morozov, and A. K. Geim, *PNAS* **102**, 10451 (2005).
- ¹⁶ T. Cao, F. Zhao, and S. G. Louie, *Physical review letters* **119**, 076401 (2017).
- ¹⁷ G. D. Nguyen, H.-Z. Tsai, A. A. Omrani, T. Marangoni, M. Wu, D. J. Rizzo, G. F. Rodgers, R. R. Cloke, R. A. Durr, Y. Sakai, *et al.*, *Nature nanotechnology* **12**, 1077 (2017).
- ¹⁸ M. Y. Han, B. Özyilmaz, Y. Zhang, and P. Kim, *Phys. Rev. Lett.* **98**, 206805 (2007).
- ¹⁹ S. Y. Zhou, G.-H. Gweon, A. Fedorov, d. First, P. N. W. De Heer, D.-H. Lee, F. Guinea, A. C. Neto, and A. Lanzara, *Nature materials* **6**, 770 (2007).
- ²⁰ F. Xia, D. B. Farmer, Y.-m. Lin, and P. Avouris, *Nano letters* **10**, 715 (2010).
- ²¹ Y.-C. Chen, T. Cao, C. Chen, Z. Pedramrazi, D. Haberer, D. G. De Oteyza, F. R. Fischer, S. G. Louie, and M. F. Crommie, *Nature nanotechnology* **10**, 156 (2015).
- ²² M. M. Ugeda, A. J. Bradley, S.-F. Shi, H. Felipe, Y. Zhang, D. Y. Qiu, W. Ruan, S.-K. Mo, Z. Hussain, Z.-X. Shen, *et al.*, *Nature materials* **13**, 1091 (2014).
- ²³ L. Brey and H. A. Fertig, *Phys. Rev. B* **73**, 235411 (2006).
- ²⁴ S. Prabhakar, R. Melnik, and L. Bonilla, *Phys. Rev. B* **93**, 115417 (2016).
- ²⁵ S. Prabhakar, R. Melnik, L. L. Bonilla, and S. Badu, *Phys. Rev. B* **90**, 205418 (2014).
- ²⁶ V. B. Shenoy, C. D. Reddy, A. Ramasubramaniam, and Y. W. Zhang, *Phys. Rev. Lett.* **101**, 245501 (2008).
- ²⁷ S. Prabhakar, R. Melnik, and L. Bonilla, *The European Physical Journal B* **90**, 92 (2017).
- ²⁸ S. Prabhakar and R. Melnik, *Journal of Physics: Condensed Matter* **27**, 435801 (2015).
- ²⁹ Z. H. Ni, W. Chen, X. F. Fan, J. L. Kuo, T. Yu, A. T. S. Wee, and Z. X. Shen, *Phys. Rev. B* **77**, 115416 (2008).
- ³⁰ R. Carrillo-Bastos, C. León, D. Faria, A. Latgé, E. Y. Andrei, and N. Sandler, *Phys. Rev. B* **94**, 125422 (2016).
- ³¹ H. Lim, J. Jung, R. S. Ruoff, and Y. Kim, *Nature communications* **6**, 8601 (2015).
- ³² M. S. Bronsgeest, N. Bendiab, S. Mathur, A. Kimouche, H. T. Johnson, J. Coraux, and P. Pochet, *Nano letters* **15**, 5098 (2015).
- ³³ E. Cerda and L. Mahadevan, *Phys. Rev. Lett.* **90**, 074302 (2003).
- ³⁴ R. J. T. Nicholl, N. V. Lavrik, I. Vlasiouk, B. R. Srijanto, and K. I. Bolotin, *Phys. Rev. Lett.* **118**, 266101 (2017).
- ³⁵ Deepika, T. J. D. Kumar, A. Shukla, and R. Kumar, *Phys. Rev. B* **91**, 115428 (2015).
- ³⁶ P. Wagner, C. P. Ewels, J.-J. Adjizian, L. Magaud, P. Pochet, S. Roche, A. Lopez-Bezanilla, V. V. Ivanovskaya, A. Yaya, M. Rayson, *et al.*, *The Journal of Physical Chemistry C* **117**, 26790 (2013).
- ³⁷ B. Zeng, Y. Dong, Y. Yi, D. Li, S. Zhang, and M. Long, *Journal of Physics: Condensed Matter* **31**, 165502 (2019).
- ³⁸ B. Zeng, M. Long, Y. Dong, J. Xiao, S. Zhang, Y. Yi, and Y. Gao, *Journal of Physics: Condensed Matter* **31**, 295702 (2019).
- ³⁹ C. P. Herrero and R. Ramírez, *Physical Review B* **97**, 195433 (2018).
- ⁴⁰ D. Yllanes, S. S. Bhabesh, D. R. Nelson, and M. J. Bowick, *Nature Communications* **8**, 1381 (2017).
- ⁴¹ R. Faccio, P. A. Denis, H. Pardo, C. Goyenola, and A. W. Mombrú, *Journal of Physics: Condensed Matter* **21**, 285304 (2009).
- ⁴² J.-W. Jiang, J.-S. Wang, and B. Li, *Physical Review B* **80**, 113405 (2009).
- ⁴³ H. Zhao, K. Min, and N. Aluru, *Nano letters* **9**, 3012 (2009).
- ⁴⁴ R. A. Bizao, T. Botari, E. Perim, N. M. Pugno, and D. S. Galvao, *Carbon* **119**, 431 (2017).
- ⁴⁵ A. Sgouros, G. Kalosakas, K. Papagelis, and C. Galiotis, *Scientific reports* **8**, 9593 (2018).
- ⁴⁶ M. Hossain, T. Hao, and B. Silverman, *Journal of Physics: Condensed Matter* **30**, 055901 (2018).
- ⁴⁷ R. J. Nicholl, N. V. Lavrik, I. Vlasiouk, B. R. Srijanto, and K. I. Bolotin, *Physical review letters* **118**, 266101 (2017).
- ⁴⁸ M. J. Bowick, A. Košmrlj, D. R. Nelson, and R. Sknepnek, *Physical Review B* **95**, 104109 (2017).

- ⁴⁹ D. Wan, D. R. Nelson, and M. J. Bowick, *Physical Review B* **96**, 014106 (2017).
- ⁵⁰ O. Blakslee, D. Proctor, E. Seldin, G. Spence, and T. Weng, *Journal of applied physics* **41**, 3373 (1970).
- ⁵¹ I. Frank, D. M. Tanenbaum, A. M. van der Zande, and P. L. McEuen, *Journal of Vacuum Science & Technology B: Microelectronics and Nanometer Structures Processing, Measurement, and Phenomena* **25**, 2558 (2007).
- ⁵² C. Gómez-Navarro, M. Burghard, and K. Kern, *Nano letters* **8**, 2045 (2008).
- ⁵³ C. Lee, X. Wei, J. W. Kysar, and J. Hone, *science* **321**, 385 (2008).
- ⁵⁴ G. Van Lier, C. Van Alsenoy, V. Van Doren, and P. Geerlings, *Chemical Physics Letters* **326**, 181 (2000).
- ⁵⁵ E. Konstantinova, S. O. Dantas, and P. M. Barone, *Physical Review B* **74**, 035417 (2006).
- ⁵⁶ E. Hernandez, C. Goze, P. Bernier, and A. Rubio, *Physical Review Letters* **80**, 4502 (1998).
- ⁵⁷ D. G. Papageorgiou, I. A. Kinloch, and R. J. Young, *Progress in Materials Science* **90**, 75 (2017).
- ⁵⁸ A. Falin, Q. Cai, E. J. Santos, D. Scullion, D. Qian, R. Zhang, Z. Yang, S. Huang, K. Watanabe, T. Taniguchi, *et al.*, *Nature communications* **8**, 15815 (2017).
- ⁵⁹ D. Zhu, Y. Ren, G. Liao, S. Jiang, F. Liu, J. Guo, and G. Xu, *Journal of Applied Polymer Science* **134**, 45332 (2017).
- ⁶⁰ G. Wang, Z. Dai, Y. Wang, P. Tan, L. Liu, Z. Xu, Y. Wei, R. Huang, and Z. Zhang, *Physical review letters* **119**, 036101 (2017).
- ⁶¹ K. Choudhary, G. Cheon, E. Reed, and F. Tavazza, *Physical Review B* **98**, 014107 (2018).
- ⁶² P. Giannozzi, S. Baroni, N. Bonini, M. Calandra, R. Car, C. Cavazzoni, D. Ceresoli, G. L. Chiarotti, M. Cococcioni, I. Dabo, A. Dal Corso, S. de Gironcoli, S. Fabris, G. Fratesi, R. Gebauer, U. Gerstmann, C. Gougousis, A. Kokalj, M. Lazzeri, L. Martin-Samos, N. Marzari, F. Mauri, R. Mazzarello, S. Paolini, A. Pasquarello, L. Paulatto, C. Sbraccia, S. Scandolo, G. Sclauzero, A. P. Seitsonen, A. Smogunov, P. Umari, and R. M. Wentzcovitch, *Journal of Physics: Condensed Matter* **21**, 395502 (2009).
- ⁶³ J. P. Perdew, K. Burke, and M. Ernzerhof, *Phys. Rev. Lett.* **77**, 3865 (1996).
- ⁶⁴ S. Grimme, *Journal of computational chemistry* **27**, 1787 (2006).
- ⁶⁵ A. Kokalj, *Computational Materials Science* **28**, 155 (2003).
- ⁶⁶ D. J. Rizzo, G. Veber, T. Cao, C. Bronner, T. Chen, F. Zhao, H. Rodriguez, S. G. Louie, M. F. Crommie, and F. R. Fischer, *Nature* **560**, 204 (2018).
- ⁶⁷ O. Gröning, S. Wang, X. Yao, C. A. Pignedoli, G. Borin Barin, C. Daniels, A. Cupo, V. Meunier, X. Feng, A. Narita, K. Müllen, P. Ruffieux, and R. Fasel, *Nature* **560**, 209 (2018).
- ⁶⁸ S. Prabhakar and R. Melnik, *Scientific reports* **7**, 17365 (2017).
- ⁶⁹ I. Burmistrov, I. Gornyi, V. Y. Kachorovskii, M. Katsnelson, J. Los, and A. Mirlin, *Physical Review B* **97**, 125402 (2018).

